



## Features

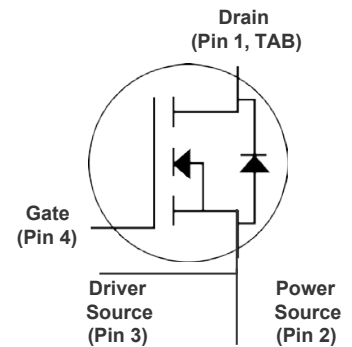
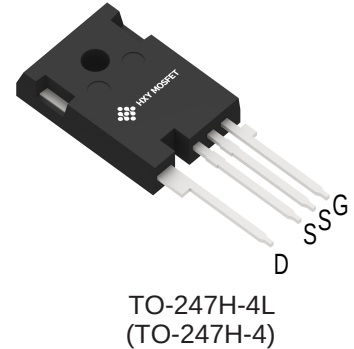
- 3rd generation SiC MOSFET technology
- Optimized package with separate driver source pin
- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery ( $Q_{rr}$ )
- Halogen free, RoHS compliant

## Benefits

- Reduce switching losses and minimize gate ringing
- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

## Applications

- Renewable energy
- EV battery chargers
- High voltage DC/DC converters
- Switch Mode Power Supplies



| Ordering Part Number | Package                   | Qty(PCS) | $T_J, T_{stg}$ Range |
|----------------------|---------------------------|----------|----------------------|
| NVH4L080N120SC1      | TO-247H-4L<br>(TO-247H-4) | 30       | -55 - 150 °C         |
| NVH4L080N120SC1-A    | TO-247H-4L<br>(TO-247H-4) | 30       | -40 - 175 °C         |

## Maximum Ratings ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

| Symbol         | Parameter                                  | Value       | Unit | Test Conditions                                     | Note    |
|----------------|--------------------------------------------|-------------|------|-----------------------------------------------------|---------|
| $V_{DSmax}$    | Drain - Source Voltage                     | 1200        | V    | $V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$ |         |
| $V_{GSmax}$    | Gate - Source Voltage (dynamic)            | -8/+19      | V    | AC ( $f > 1\text{ Hz}$ )                            | Note: 1 |
| $V_{GSop}$     | Gate - Source Voltage (static)             | -4/+15      | V    | Static                                              | Note: 2 |
| $I_D$          | Continuous Drain Current                   | 32          | A    | $V_{GS} = 15\text{ V}, T_C = 25^\circ\text{C}$      | Fig. 19 |
|                |                                            | 23          |      | $V_{GS} = 15\text{ V}, T_C = 100^\circ\text{C}$     |         |
| $I_{D(pulse)}$ | Pulsed Drain Current                       | 80          | A    | Pulse width $t_p$ limited by $T_{Jmax}$             | Fig. 22 |
| $P_D$          | Power Dissipation                          | 136         | W    | $T_C = 25^\circ\text{C}, T_J = 175^\circ\text{C}$   | Fig. 20 |
| $T_J, T_{stg}$ | Operating Junction and Storage Temperature | -40 to +175 | °C   |                                                     |         |
| $T_L$          | Solder Temperature                         | 260         | °C   | 1.6mm (0.063") from case for 10s                    |         |

Note (1): When using MOSFET Body Diode  $V_{GSmax} = -4\text{V}/+19\text{V}$

Note (2): MOSFET can also safely operate at  $0/+15\text{ V}$



**Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise specified)

| Symbol        | Parameter                                  | Min. | Typ. | Max. | Unit          | Test Conditions                                                                                                                                                      | Note         |
|---------------|--------------------------------------------|------|------|------|---------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage             | 1200 |      |      | V             | $V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$                                                                                                                  |              |
| $V_{GS(th)}$  | Gate Threshold Voltage                     | 1.8  | 2.5  | 3.6  | V             | $V_{DS} = V_{GS}, I_D = 5\text{ mA}$                                                                                                                                 | Fig. 11      |
|               |                                            |      | 2.2  |      | V             | $V_{DS} = V_{GS}, I_D = 5\text{ mA}, T_J = 175^\circ\text{C}$                                                                                                        |              |
| $I_{DSS}$     | Zero Gate Voltage Drain Current            |      | 1    | 50   | $\mu\text{A}$ | $V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$                                                                                                                        |              |
| $I_{GSS}$     | Gate-Source Leakage Current                |      | 10   | 250  | nA            | $V_{GS} = 15\text{ V}, V_{DS} = 0\text{ V}$                                                                                                                          |              |
| $R_{DS(on)}$  | Drain-Source On-State Resistance           |      | 75   | 90   | m $\Omega$    | $V_{GS} = 15\text{ V}, I_D = 20\text{ A}$                                                                                                                            | Fig. 4, 5, 6 |
|               |                                            |      | 120  |      |               | $V_{GS} = 15\text{ V}, I_D = 20\text{ A}, T_J = 175^\circ\text{C}$                                                                                                   |              |
| $g_{fs}$      | Transconductance                           |      | 12   |      | S             | $V_{DS} = 20\text{ V}, I_{DS} = 20\text{ A}$                                                                                                                         | Fig. 7       |
|               |                                            |      | 13   |      |               | $V_{DS} = 20\text{ V}, I_{DS} = 20\text{ A}, T_J = 175^\circ\text{C}$                                                                                                |              |
| $C_{iss}$     | Input Capacitance                          |      | 1390 |      | pF            | $V_{GS} = 0\text{ V}, V_{DS} = 1000\text{ V}$<br>$f = 1\text{ MHz}$<br>$V_{AC} = 25\text{ mV}$                                                                       | Fig. 17, 18  |
| $C_{oss}$     | Output Capacitance                         |      | 58   |      |               |                                                                                                                                                                      |              |
| $C_{rss}$     | Reverse Transfer Capacitance               |      | 2    |      |               |                                                                                                                                                                      |              |
| $E_{oss}$     | $C_{oss}$ Stored Energy                    |      | 33   |      | $\mu\text{J}$ |                                                                                                                                                                      | Fig. 16      |
| $E_{ON}$      | Turn-On Switching Energy (Body Diode FWD)  |      | 270  |      | $\mu\text{J}$ | $V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}, I_D = 20\text{ A},$<br>$R_{G(ext)} = 0\text{ }\Omega, L = 156\text{ }\mu\text{H}, T_J = 150^\circ\text{C}$ | Fig. 26, 29  |
| $E_{OFF}$     | Turn-Off Switching Energy (Body Diode FWD) |      | 77   |      |               |                                                                                                                                                                      |              |
| $t_{d(on)}$   | Turn-On Delay Time                         |      | 30   |      | ns            | $V_{DD} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$<br>$I_D = 20\text{ A}, R_{G(ext)} = 0\text{ }\Omega,$<br>Timing relative to $V_{DS}$ Inductive load        | Fig. 27, 28  |
| $t_r$         | Rise Time                                  |      | 14   |      |               |                                                                                                                                                                      |              |
| $t_{d(off)}$  | Turn-Off Delay Time                        |      | 38   |      |               |                                                                                                                                                                      |              |
| $t_f$         | Fall Time                                  |      | 10   |      |               |                                                                                                                                                                      |              |
| $R_{G(int)}$  | Internal Gate Resistance                   |      | 9.0  |      | $\Omega$      | $f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$                                                                                                                            |              |
| $Q_{gs}$      | Gate to Source Charge                      |      | 17   |      | nC            | $V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$<br>$I_D = 20\text{ A}$<br>Per IEC60747-8-4 pg 21                                                           | Fig. 12      |
| $Q_{gd}$      | Gate to Drain Charge                       |      | 18   |      |               |                                                                                                                                                                      |              |
| $Q_g$         | Total Gate Charge                          |      | 53   |      |               |                                                                                                                                                                      |              |

**Reverse Diode Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise specified)

| Symbol         | Parameter                        | Typ. | Max. | Unit | Test Conditions                                                                                                                                  | Note          |
|----------------|----------------------------------|------|------|------|--------------------------------------------------------------------------------------------------------------------------------------------------|---------------|
| $V_{SD}$       | Diode Forward Voltage            | 4.5  |      | V    | $V_{GS} = -4\text{ V}, I_{SD} = 10\text{ A}$                                                                                                     | Fig. 8, 9, 10 |
|                |                                  | 4.0  |      | V    | $V_{GS} = -4\text{ V}, I_{SD} = 10\text{ A}, T_J = 175^\circ\text{C}$                                                                            |               |
| $I_S$          | Continuous Diode Forward Current |      | 26   | A    | $V_{GS} = -4\text{ V}, T_J = 25^\circ\text{C}$                                                                                                   | Note 1        |
| $I_{S, pulse}$ | Diode pulse Current              | 80   |      | A    | $V_{GS} = -4\text{ V},$ pulse width $t_p$ limited by $T_{Jmax}$                                                                                  | Note 1        |
| $t_{rr}$       | Reverse Recover time             | 20   |      | ns   | $V_{GS} = -4\text{ V}, I_{SD} = 20\text{ A}, V_R = 800\text{ V}$<br>$\text{diff}/\text{dt} = 3600\text{ A}/\mu\text{s}, T_J = 150^\circ\text{C}$ | Note 1        |
| $Q_{rr}$       | Reverse Recovery Charge          | 254  |      | nC   |                                                                                                                                                  |               |
| $I_{rrm}$      | Peak Reverse Recovery Current    | 18   |      | A    |                                                                                                                                                  |               |

**Thermal Characteristics**

| Symbol          | Parameter                                   | Max. | Unit                      | Test Conditions | Note    |
|-----------------|---------------------------------------------|------|---------------------------|-----------------|---------|
| $R_{\theta JC}$ | Thermal Resistance from Junction to Case    | 1.1  | $^\circ\text{C}/\text{W}$ |                 | Fig. 21 |
| $R_{\theta JA}$ | Thermal Resistance From Junction to Ambient | 40   |                           |                 |         |



## Typical Performance

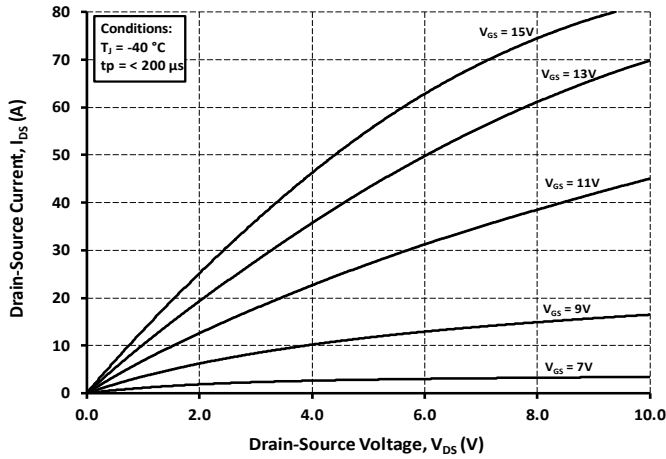


Figure 1. Output Characteristics  $T_J = -40\text{ }^{\circ}\text{C}$

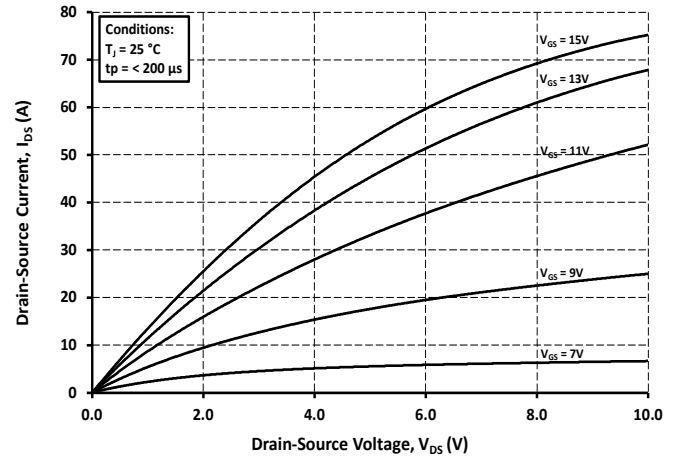


Figure 2. Output Characteristics  $T_J = 25\text{ }^{\circ}\text{C}$

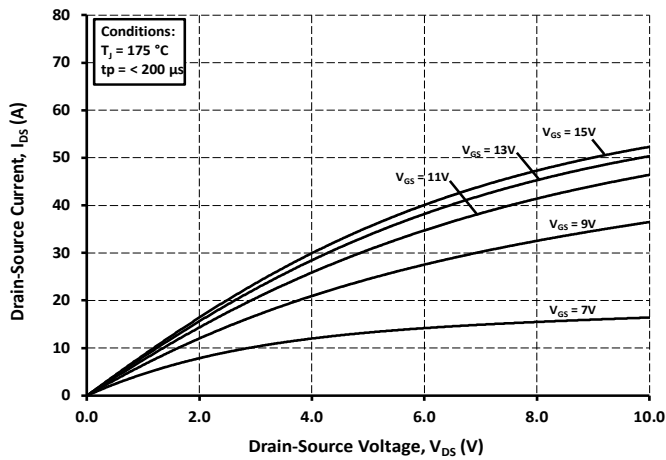


Figure 3. Output Characteristics  $T_J = 175\text{ }^{\circ}\text{C}$

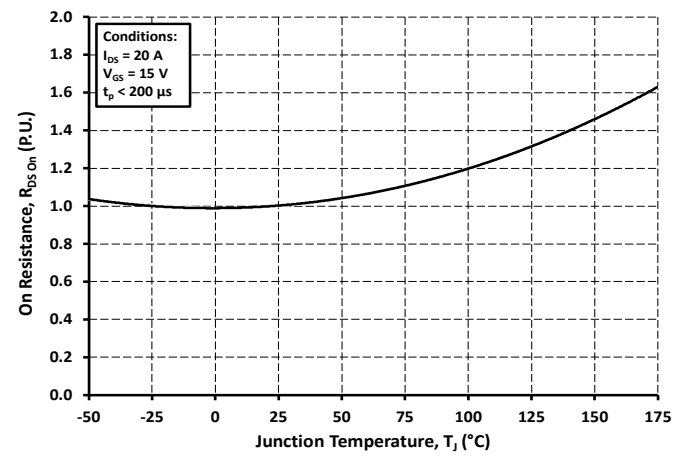


Figure 4. Normalized On-Resistance vs. Temperature

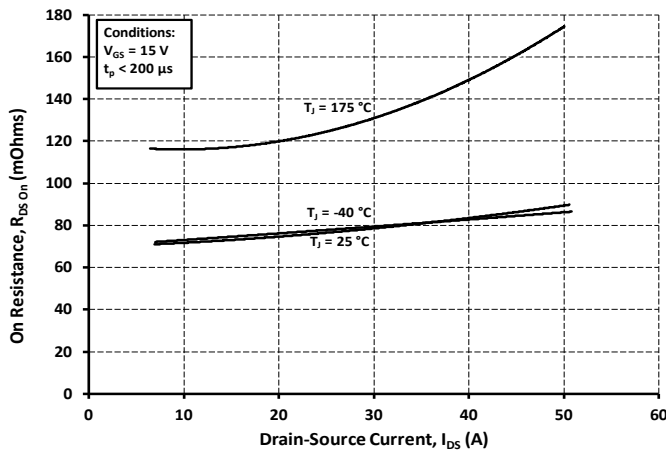


Figure 5. On-Resistance vs. Drain Current  
For Various Temperatures

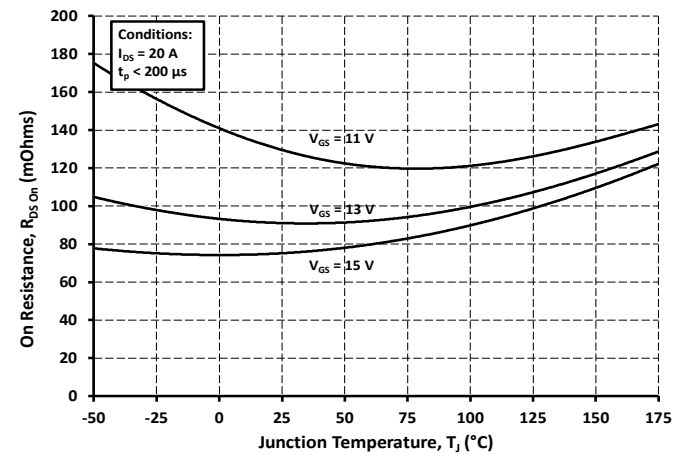


Figure 6. On-Resistance vs. Temperature  
For Various Gate Voltage



## Typical Performance

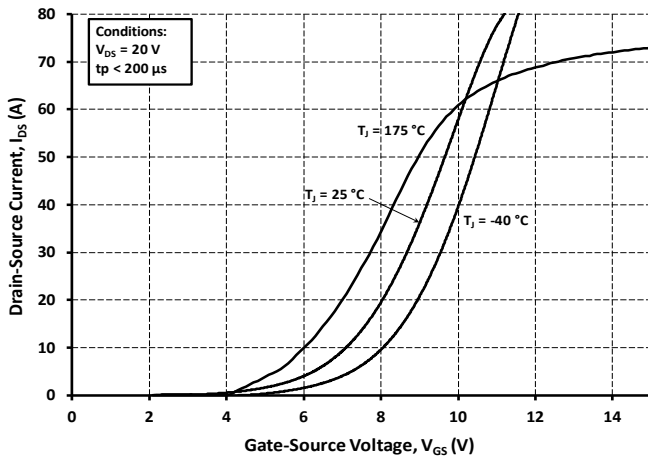


Figure 7. Transfer Characteristic for Various Junction Temperatures

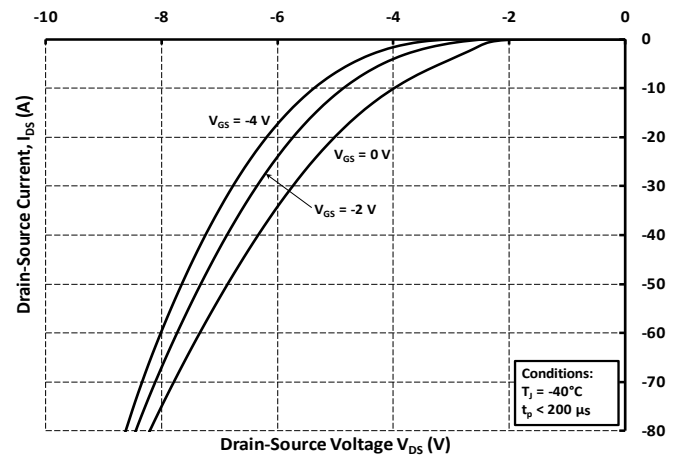


Figure 8. Body Diode Characteristic at -40 °C

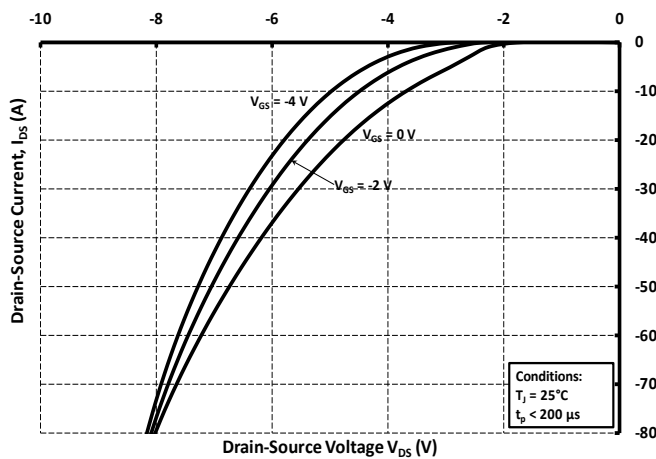


Figure 9. Body Diode Characteristic at 25 °C

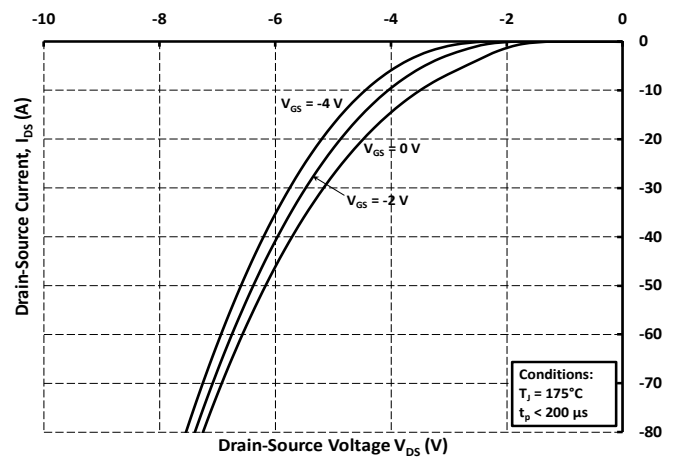


Figure 10. Body Diode Characteristic at 175 °C

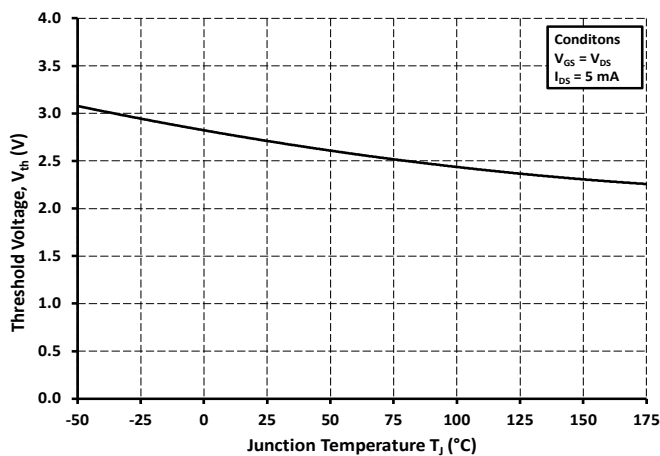


Figure 11. Threshold Voltage vs. Temperature

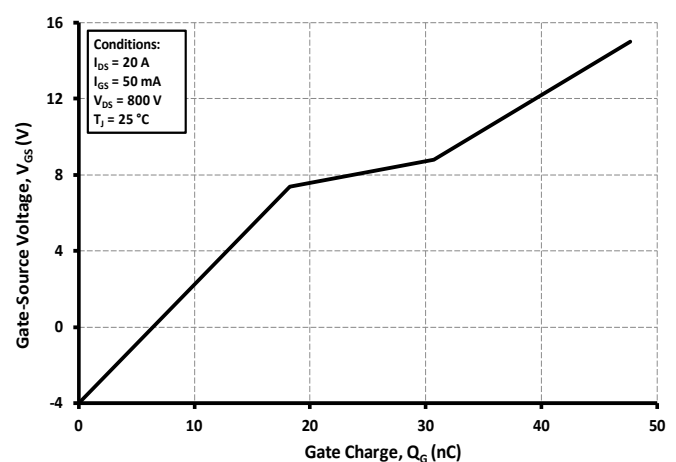


Figure 12. Gate Charge Characteristics



## Typical Performance

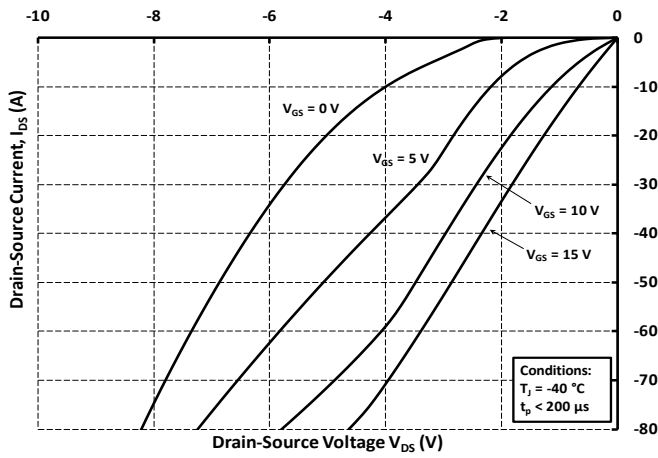


Figure 13. 3rd Quadrant Characteristic at -40 °C

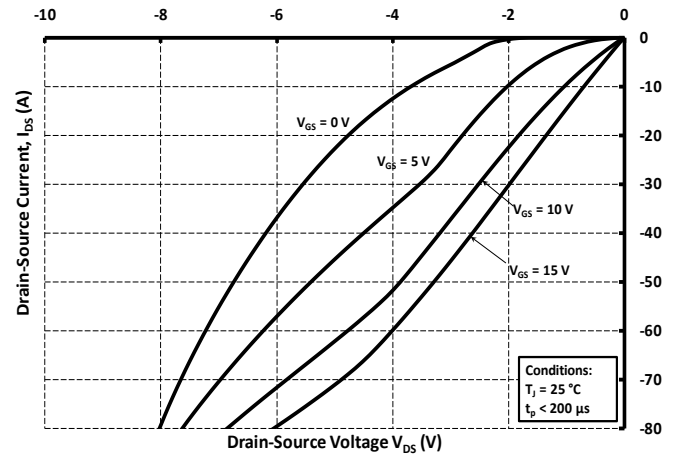


Figure 14. 3rd Quadrant Characteristic at 25 °C

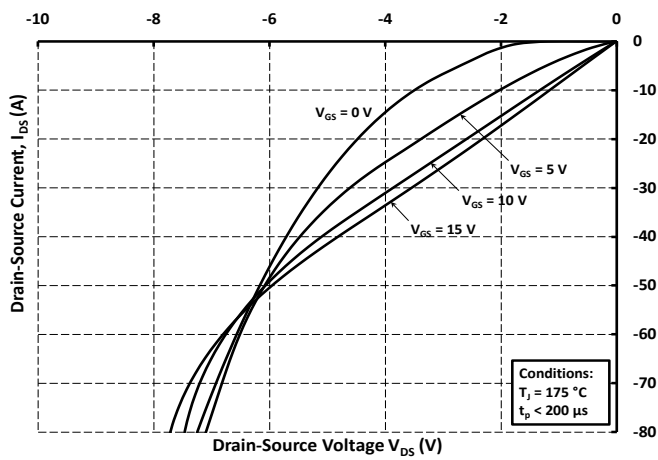


Figure 15. 3rd Quadrant Characteristic at 175 °C

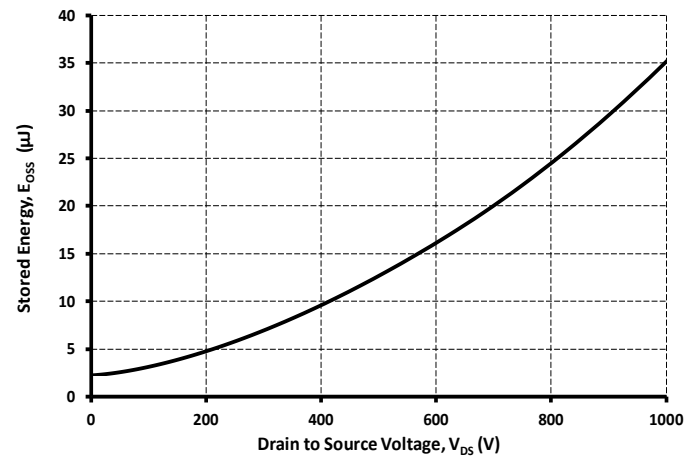


Figure 16. Output Capacitor Stored Energy

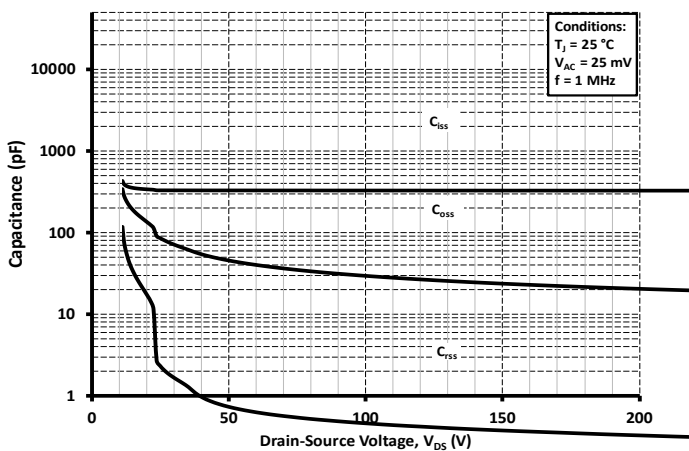


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

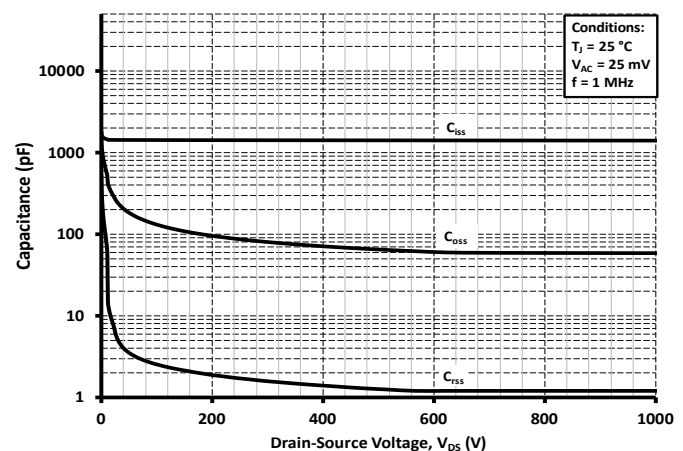


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1000V)



## Typical Performance

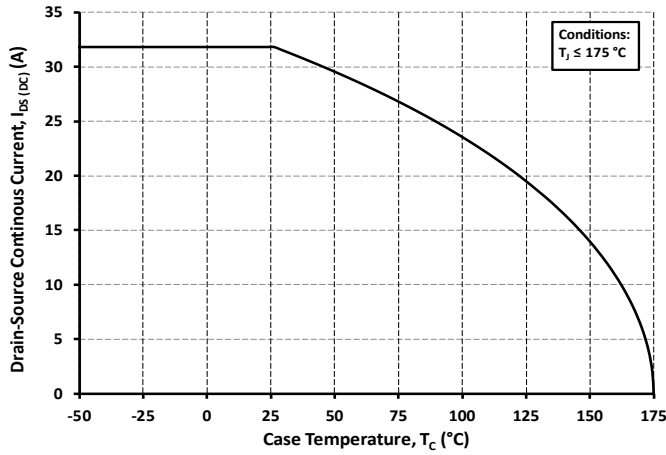


Figure 19. Continuous Drain Current Derating vs. Case Temperature

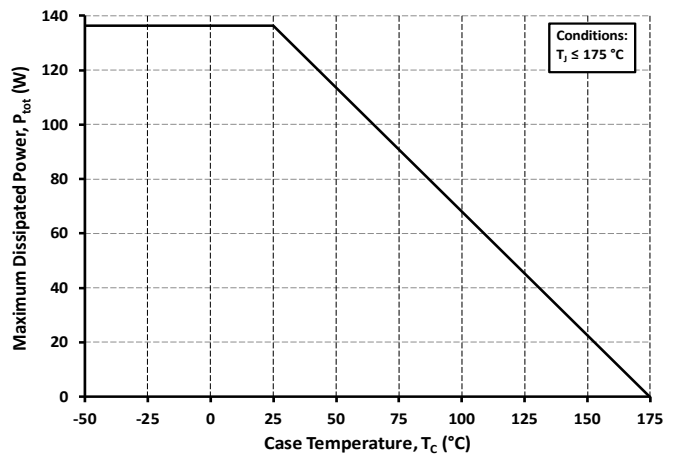


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

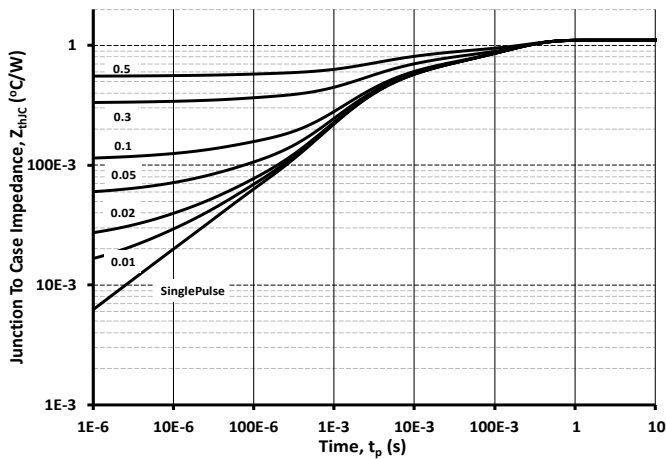


Figure 21. Transient Thermal Impedance (Junction - Case)

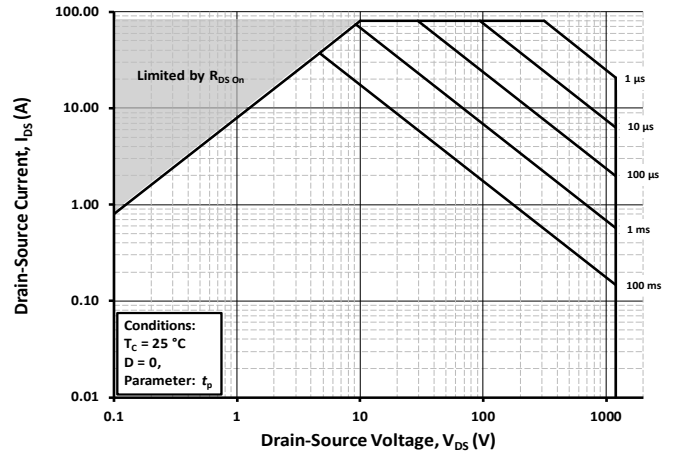


Figure 22. Safe Operating Area

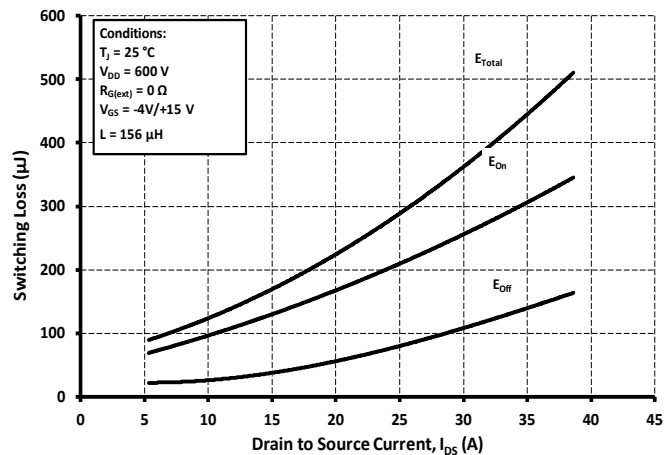


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 600V$ )

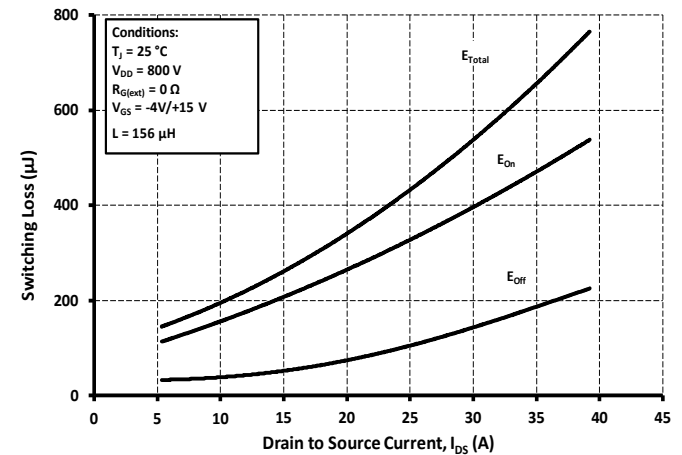


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 800V$ )



## Typical Performance

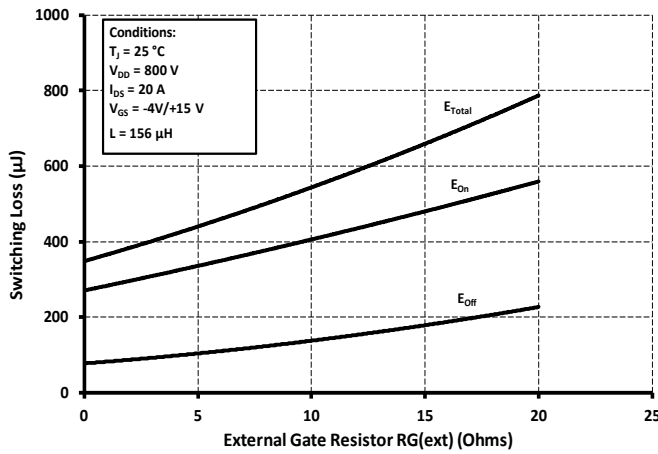


Figure 25. Clamped Inductive Switching Energy vs.  $R_{G(\text{ext})}$

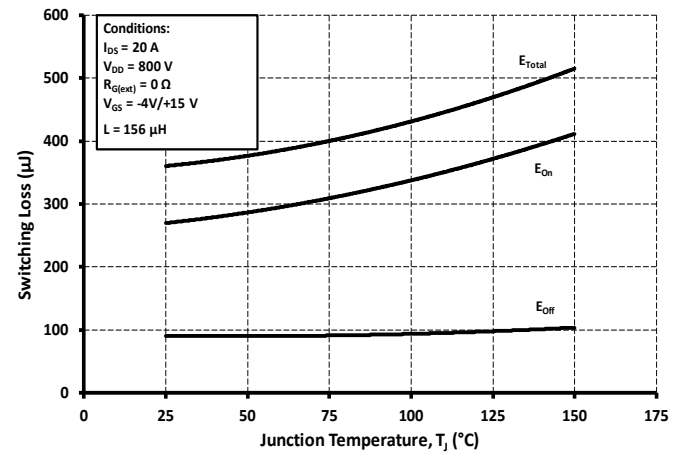


Figure 26. Clamped Inductive Switching Energy vs. Temperature

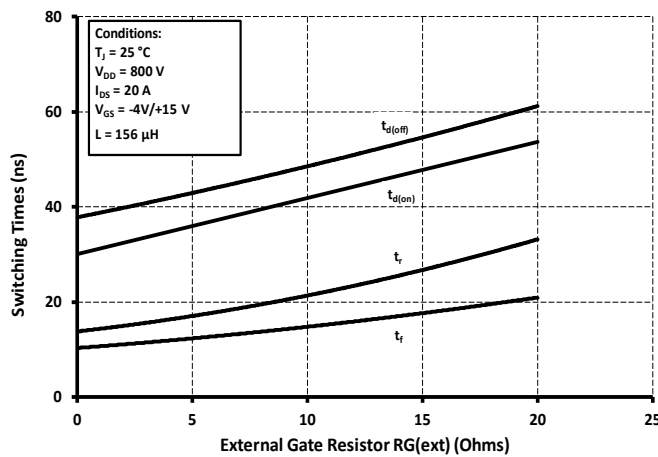


Figure 27. Switching Times vs.  $R_{G(\text{ext})}$

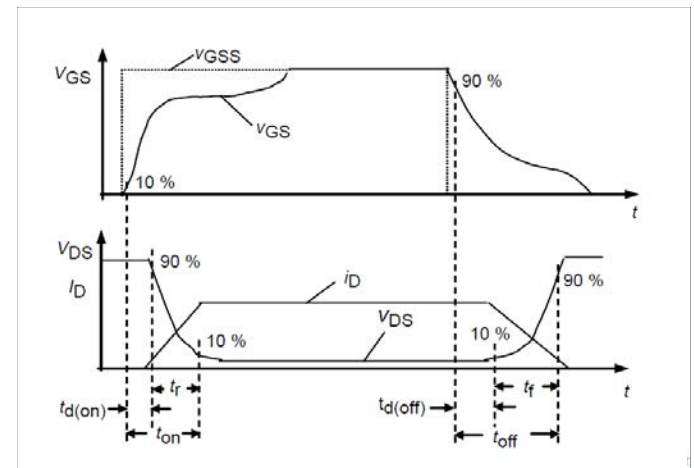


Figure 28. Switching Times Definition



## Test Circuit Schematic

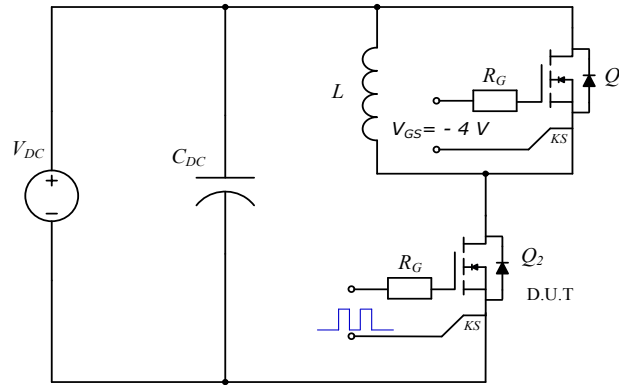


Figure 29. Clamped Inductive Switching  
Waveform Test Circuit

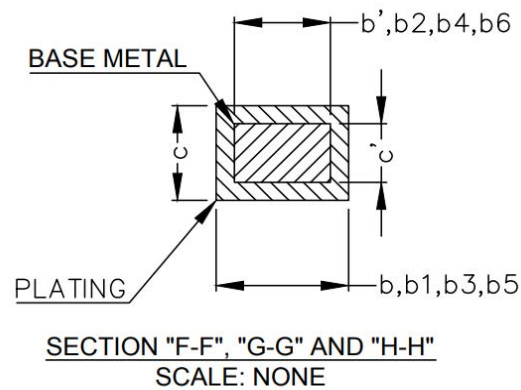
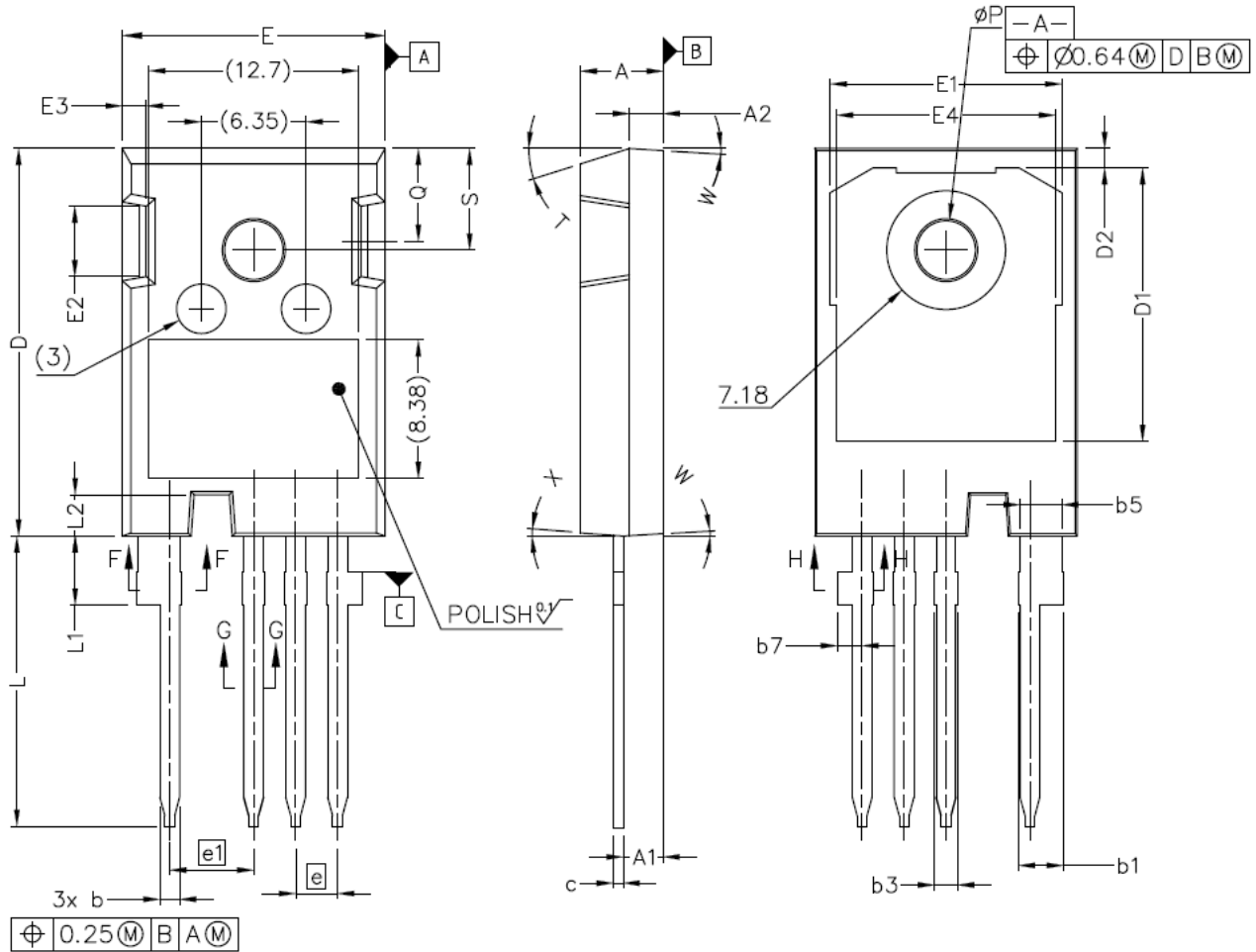
Note (3): Turn-off and Turn-on switching energy and timing values measured using SiC MOSFET Body Diode as shown above.





## Package Dimensions

Package TO-247H-4L(TO-247H-4)





## Package Dimensions

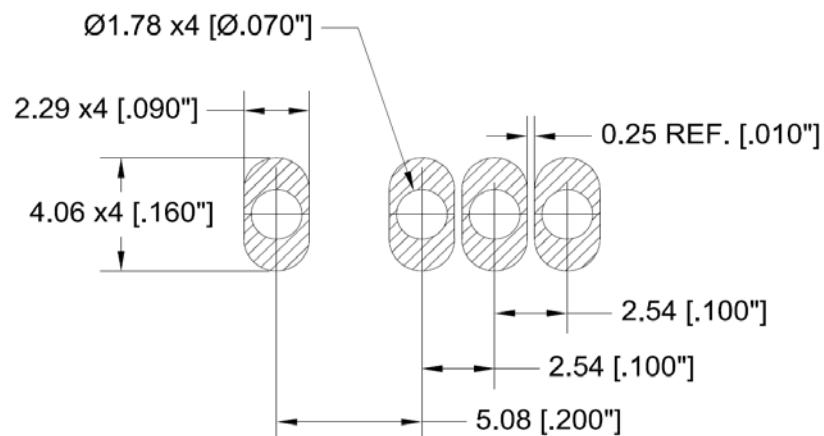
Package TO-247H-4L(TO-247H-4)

NOTE ;

1. ALL METAL SURFACES: TIN PLATED, EXCEPT AREA OF CUT
2. DIMENSIONING & TOLERANCEING CONFIRM TO ASME Y14.5M-1994.
3. ALL DIMENSIONS ARE IN MILLIMETERS.  
ANGLES ARE IN DEGREES.
4. 'N' IS THE NUMBER OF TERMINAL POSITIONS

| SYM | MILLIMETERS |       |
|-----|-------------|-------|
|     | MIN         | MAX   |
| A   | 4.83        | 5.21  |
| A1  | 2.29        | 2.54  |
| A2  | 1.91        | 2.16  |
| b`  | 1.07        | 1.28  |
| b   | 1.07        | 1.33  |
| b1  | 2.39        | 2.94  |
| b2  | 2.39        | 2.84  |
| b3  | 1.07        | 1.60  |
| b4  | 1.07        | 1.50  |
| b5  | 2.39        | 2.69  |
| b6  | 2.39        | 2.64  |
| b7  | 1.30        | 1.70  |
| c`  | 0.55        | 0.65  |
| c   | 0.55        | 0.68  |
| D   | 23.30       | 23.60 |
| D1  | 16.25       | 17.65 |
| D2  | 0.95        | 1.25  |
| E   | 15.75       | 16.13 |

| SYM | MILLIMETERS |       |
|-----|-------------|-------|
|     | MIN         | MAX   |
| E1  | 13.10       | 14.15 |
| E2  | 3.68        | 5.10  |
| E3  | 1.00        | 1.90  |
| E4  | 12.38       | 13.43 |
| e   | 2.54 BSC    |       |
| e1  | 5.08 BSC    |       |
| N*  | 4           |       |
| L   | 17.31       | 17.82 |
| L1  | 3.97        | 4.37  |
| L2  | 2.35        | 2.65  |
| Ø P | 3.51        | 3.65  |
| Q   | 5.49        | 6.00  |
| S   | 6.04        | 6.30  |
| T   | 17.5° REF.  |       |
| W   | 3.5° REF.   |       |
| X   | 4° REF.     |       |





### **Attention**

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.